

L Number	Hits	Search Text	DB	Time stamp
157	1974	(polish\$3 planariz\$5) and (chang\$3 near5 (fluid solvent slurry))	USPAT	2004/05/07 07:29
158	392	(polish\$3 planariz\$5) same (chang\$3 near5 (fluid solvent slurry))	USPAT	2004/05/07 07:30
159	324	(polish\$3 planariz\$5) same (chang\$3 near5 (fluid solvent slurry))not (438/14 216/38 216/84 216/86) and (chang\$3 near5 (fluid solvent slurry))	USPAT	2004/05/07 07:30
-	114	(156/345.12,156/345.31, 156/345.32).ccls.	USPAT	2004/05/07 05:39
-	1667	438/692.ccls. 414/(271,940,941,938).ccls. 451/66 216/88	USPAT	2002/10/22 12:28
-	1708	((156/345.12,156/345.31, 156/345.32).ccls.) (438/692.ccls. 414/(271,940,941,938).ccls. 451/66 216/88)	USPAT	2002/12/28 09:48
-	194	((156/345.12,156/345.31, 156/345.32).ccls.) (438/692.ccls. 414/(271,940,941,938).ccls. 451/66 216/88)) and ((thickness depth metrology) same (clean\$3 buff\$3 wash\$3 rins\$3))	USPAT	2002/10/22 12:30
-	408	((156/345.12,156/345.31, 156/345.32).ccls.) (438/692.ccls. 414/(271,940,941,938).ccls. 451/66 216/88)) and (multiple plural\$3) with (polish\$3 clean\$3)	USPAT	2002/10/22 12:34
-	59	((156/345.12,156/345.31, 156/345.32).ccls.) (438/692.ccls. 414/(271,940,941,938).ccls. 451/66 216/88)) and ((thickness depth metrology) same (clean\$3 buff\$3 wash\$3 rins\$3))) and ((156/345.12,156/345.31, 156/345.32).ccls.) (438/692.ccls. 414/(271,940,941,938).ccls. 451/66 216/88)) and (multiple plural\$3) with (polish\$3 clean\$3))	USPAT	2002/10/22 12:31
-	211	((156/345.12,156/345.31, 156/345.32).ccls.) (438/692.ccls. 414/(271,940,941,938).ccls. 451/66 216/88)) and ((thickness depth metrology) same (clean\$3 buff\$3 wash\$3 rins\$3))) and ((156/345.12,156/345.31, 156/345.32).ccls.) (438/692.ccls. 414/(271,940,941,938).ccls. 451/66 216/88)) and (multiple plural\$3) with (polish\$3 clean\$3)) and (elevator cassette vertical\$2)	USPAT	2002/10/22 12:32
-	31	((156/345.12,156/345.31, 156/345.32).ccls.) (438/692.ccls. 414/(271,940,941,938).ccls. 451/66 216/88)) and ((thickness depth metrology) same (clean\$3 buff\$3 wash\$3 rins\$3))) and ((156/345.12,156/345.31, 156/345.32).ccls.) (438/692.ccls. 414/(271,940,941,938).ccls. 451/66 216/88)) and (multiple plural\$3) with (polish\$3 clean\$3)) and (elevator cassette vertical\$2)	USPAT	2002/10/22 12:33
-	38	((156/345.12,156/345.31, 156/345.32).ccls.) (438/692.ccls. 414/(271,940,941,938).ccls. 451/66 216/88)) and (multiple plural\$3) with (polish\$3 and clean\$3)	USPAT	2002/10/22 12:44
-	9770	(planariz\$5 polish\$3) same (clean\$3 rins\$3 wash\$3)	EPO; JPO; DERWENT	2002/10/22 12:53
-	1815	((planariz\$5 polish\$3) same (clean\$3 rins\$3 wash\$3)) and (semiconductor wafer)	EPO; JPO; DERWENT	2002/10/22 12:55
-	73	((planariz\$5 polish\$3) same (clean\$3 rins\$3 wash\$3)) and (semiconductor wafer)) and (thickness metrology depth width) with (clean\$3 rins\$3 wash\$3)	EPO; JPO; DERWENT	2002/10/22 12:55

-	7	((("6213853") or ("6036582") or ("6050884") or ("6110024") or ("6168683") or ("5830045") or ("5827110"))).PN.	USPAT	2002/10/31 11:23
-	2	((("2001257248") or ("81744417"))).PN.	JPO; DERWENT	2003/05/29 14:22
-	1774	((156/345.12,156/345.31,156/345.32).ccls.) (438/692.ccls.414/(271,940,941,938).ccls. 451/66 216/88)	USPAT	2002/12/28 09:48
-	1356	((156/345.12,156/345.31,156/345.32).ccls.) (438/692.ccls.414/(271,940,941,938).ccls. 451/66 216/88) ) and (metrology thickness measur\$3)	USPAT	2002/12/28 10:02
-	510	((156/345.12,156/345.31,156/345.32).ccls.) (438/692.ccls.414/(271,940,941,938).ccls. 451/66 216/88) ) and (metrology thickness measur\$3)) and (clean\$3 polish\$3) near5 (metrology thickness measur\$3)	USPAT	2002/12/28 10:01
-	0	156/345.13,156/345.16,156/345.15,ccls.	USPAT	2002/12/28 10:01
-	145	156/345.13 156/345.16 156/345.15	USPAT	2002/12/28 10:02
-	95	(156/345.13 156/345.16 156/345.15) and (metrology thickness measur\$3)	USPAT	2002/12/28 10:02
-	158	"5655954" "5337015" "5948203"	USPAT	2003/03/12 13:19
-	3	("5655954" "5337015" "5948203").pn.	USPAT	2003/03/12 13:19
-	0	(156/345.13).CCLS.	JPO; DERWENT	2003/05/29 14:22
-	51	(156/345.13).CCLS.	USPAT	2003/05/29 14:33
-	0	(156/345.12 156/345.31 156/345.32 451/66).CCLS.	USPAT	2003/05/29 14:34
-	441	((156/345.12 ) or (156/345.31 ) or (156/345.32 ) or (451/66)).CCLS.	USPAT	2003/05/29 14:34
-	437	((156/345.12 ) or (156/345.31 ) or (156/345.32 ) or (451/66)).CCLS.) not ((156/345.13).CCLS.)	USPAT	2003/05/29 14:48
-	165	"5655954" "5337015" "5948203"	USPAT	2003/05/29 14:58
-	6747	kimura-\$in. koitama-\$in. akagi-\$in.	USPAT	2003/05/29 14:59
-	390	(kimura-\$in. koitama-\$in. akagi-\$in.) and (polish\$3 planariz\$5 abrad\$3)	USPAT	2003/05/29 14:59
-	386	((kimura-\$in. koitama-\$in. akagi-\$in.) and (polish\$3 planariz\$5 abrad\$3)) not (((156/345.13).CCLS.) (((156/345.12 ) or (156/345.31 ) or (156/345.32 ) or (451/66)).CCLS.) (((156/345.12 ) or (156/345.31 ) or (156/345.32 ) or (451/66)).CCLS.) not ((156/345.13).CCLS.)))	USPAT	2003/05/29 15:01
-	234	((kimura-\$in. koitama-\$in. akagi-\$in.) and (polish\$3 planariz\$5 abrad\$3)) not (((156/345.13).CCLS.) (((156/345.12 ) or (156/345.31 ) or (156/345.32 ) or (451/66)).CCLS.) (((156/345.12 ) or (156/345.31 ) or (156/345.32 ) or (451/66)).CCLS.) not ((156/345.13).CCLS.))) and (atomiz\$5 control\$3)	USPAT	2003/05/29 15:02
-	116	((kimura-\$in. koitama-\$in. akagi-\$in.) and (polish\$3 planariz\$5 abrad\$3)) not (((156/345.13).CCLS.) (((156/345.12 ) or (156/345.31 ) or (156/345.32 ) or (451/66)).CCLS.) (((156/345.12 ) or (156/345.31 ) or (156/345.32 ) or (451/66)).CCLS.) not ((156/345.13).CCLS.))) and (atomiz\$5 control\$3)) and (wafer semiconductor)	USPAT	2003/05/29 15:02
-	9	("5665954" "5948203" "6036582" "6050884" "6227950" "5337015" "5827110" "5830045" "6110024").pn.	USPAT	2003/05/30 10:07
-	1	5655954.pn.	USPAT	2003/05/30 12:56
-	40	156/345.14	USPAT	2003/05/30 13:02
-	23	brim and (plasma with etch\$3)	USPAT	2003/05/30 13:02
-	204	156/345.12.ccls. 156/345.22.ccls.	USPAT	2003/06/09 15:15

-	251	(156/345.12.ccls. 156/345.22.ccls.)	USPAT	2003/06/09 15:21
-	30	156/345.13.ccls. ((156/345.12.ccls. 156/345.22.ccls.) 156/345.13.ccls.) and (detect\$3 monitor\$3) with thickness	USPAT	2003/06/10 08:20
-	1518	216/38 216/84 216/88 216/89	USPAT	2003/06/10 09:14
-	16	((216/38 216/84 216/88 216/89) and thickness) and "top ring"	USPAT	2003/06/10 09:15
-	1030	(216/38 216/84 216/88 216/89) and thickness	USPAT	2003/06/10 09:22
-	3	("5857893" "5733171" "6379230").pn.	USPAT	2003/06/10 11:14
-	77	156/345.15	USPAT	2003/06/10 11:15
-	43	156/345.14	USPAT	2003/06/10 11:27
-	73	156/345.26	USPAT	2003/06/10 11:27
-	1	mask\$3 with lead\$1 with polish\$3 with (rotat\$3 or turn\$3)	USPAT	2003/06/11 11:52
-	0	mask\$3 with lead\$1 with brush\$3 with (rotat\$3 or turn\$3)	USPAT	2003/06/11 11:52
-	82	mask\$3 with lead\$1 with packag\$3	USPAT	2003/06/11 13:37
-	734	control\$4 with brush\$3 with speed	USPAT	2003/06/11 13:42
-	74	(control\$4 with brush\$3 with speed) and semiconductor	USPAT	2003/06/11 13:46
-	74	((control\$4 with brush\$3 with speed) and semiconductor)	USPAT	2003/06/11 13:42
-	131	(control\$4 with brush\$3 with speed) and leads	USPAT	2003/06/11 13:58
-	0	((controller computer) with speed with brush\$3) same ("semiconductor package" "semiconductor lead")	USPAT	2003/06/11 14:00
-	0	((control\$4 computer) with speed with brush\$3) same ("semiconductor package" "semiconductor lead")	USPAT	2003/06/11 14:01
-	18	((control\$4 computer) with speed with brush\$3) same (package lead)	USPAT	2003/06/11 14:04
-	11	((control\$4 computer) with speed with brush\$3) same (package lead)	EPO; JPO; DERWENT	2003/06/11 14:05
-	3674	("semiconductor package" )	USPAT	2003/06/11 14:06
-	58	((("semiconductor package" )) and brush\$3	USPAT	2003/06/11 14:08
-	16	((("semiconductor package" )) and brush\$3) and (computer controller)	USPAT	2003/06/11 14:08
-	1	6099647.pn.	USPAT	2003/06/11 16:45
-	77	156/345.15	USPAT	2003/06/18 11:17
-	1332	451/288	USPAT	2003/06/18 12:23
-	1	5681212.pn.	USPAT	2003/06/18 12:23
-	2	("5545076" "5567199").pn.	USPAT	2003/06/19 13:09
-	11000	(smooth rough)with (polish\$3 planariz\$5 abrad\$3)	USPAT	2003/06/19 13:10
-	398	((smooth)with (polish\$3 planariz\$5 abrad\$3)) same( rough with (polish\$3 planariz\$5 abrad\$3))	USPAT	2003/06/19 13:41
-	837	((fine smooth)with (polish\$3 planariz\$5 abrad\$3)) same( (rough coarse) with (polish\$3 planariz\$5 abrad\$3))	USPAT	2003/06/19 13:57
-	86	((fine smooth)with (polish\$3 planariz\$5 abrad\$3)) same( (rough coarse) with (polish\$3 planariz\$5 abrad\$3)) and (thickness with (monitor\$3 measur\$5))	USPAT	2003/06/19 13:42
-	318	((fine smooth)with (polish\$3 planariz\$5 abrad\$3)) same( (rough coarse) with (polish\$3 planariz\$5 abrad\$3))	EPO; JPO; DERWENT	2003/06/19 13:57
-	2932	oxid\$5 with (titanium Ti) with ("titanium nitride" TiN) with (W tungsten)	USPAT	2003/06/23 14:42
-	129070	"2" and (polish\$3 abrad\$3 planariz\$5)	USPAT	2003/06/23 14:43
-	927	(oxid\$5 with (titanium Ti) with ("titanium nitride" TiN) with (W tungsten) ) and (polish\$3 abrad\$3 planariz\$5)	USPAT	2003/06/23 14:59
-	1	3855024.pn.	USPAT	2003/06/23 14:59
-	279	"eddy current" with (thickness size) with (film layer)	USPAT	2003/12/18 07:46
-	7068	156/345.12 156/345.14 156/345	USPAT	2004/05/06 14:30
-	394	156/345.12 156/345.14 156/345.15 156/345.16	USPAT	2004/05/06 15:22

-	14	((("5514245") or ("5559428") or ("5644221") or ("5659492") or ("5660672") or ("5663637") or ("5676587") or ("5731697") or ("5770948") or ("6555466") or ("6558229") or ("6579148") or ("6582282") or ("6602724"))).PN.	USPAT	2004/05/06 15:26
-	7	"1066925" "02103777" "02103779"	JPO;	2004/05/06 15:27
-	1	"1066925" "02103777" "02103779"	DERWENT	
-	3354	438/14 216/38 216/84 216/86	EPO	2004/05/06 15:27
-	85	(438/14 216/38 216/84 216/86) and (chang\$3 near5 (fluid solvent slurry))	USPAT	2004/05/07 05:39
			USPAT	2004/05/07 07:30